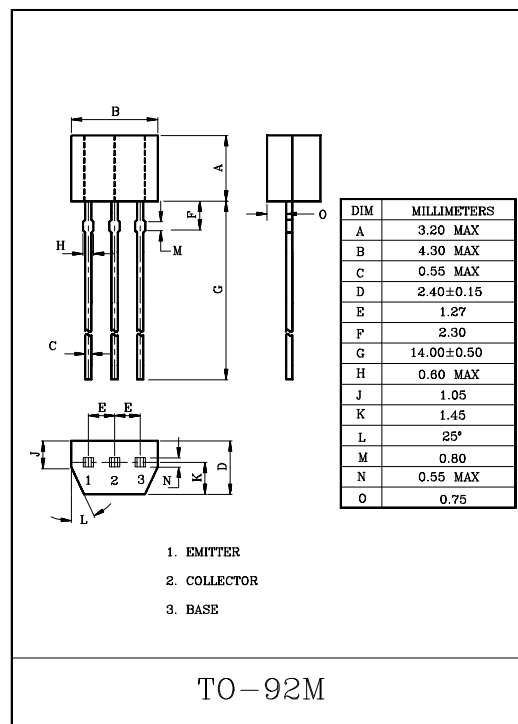
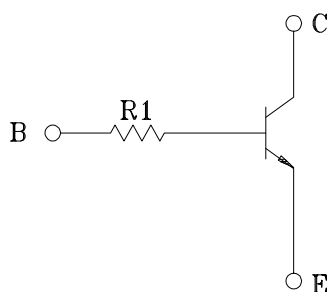


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

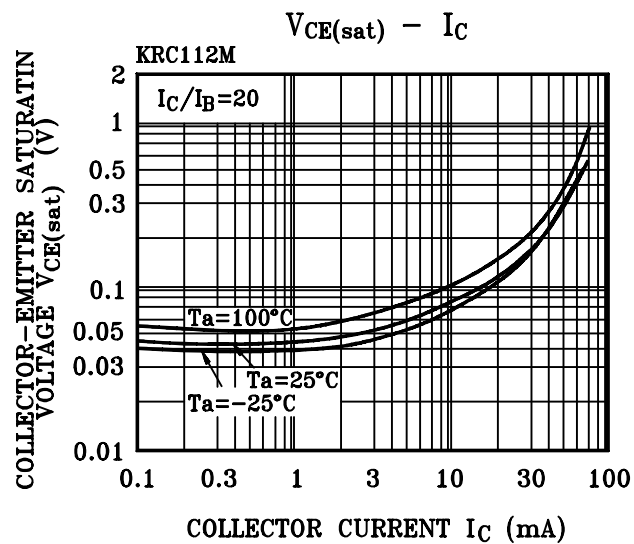
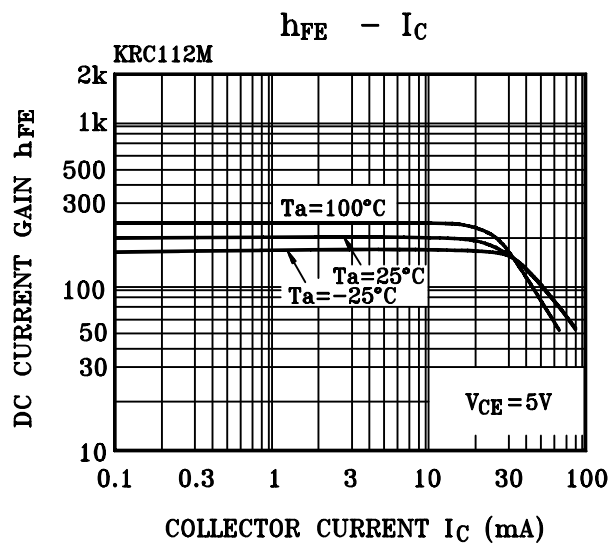
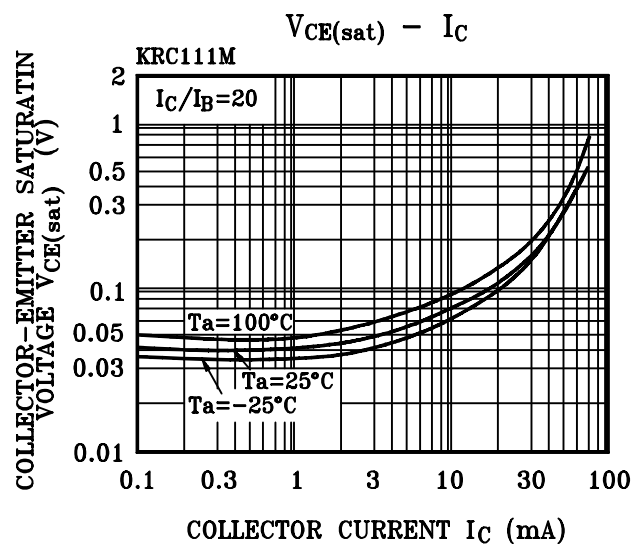
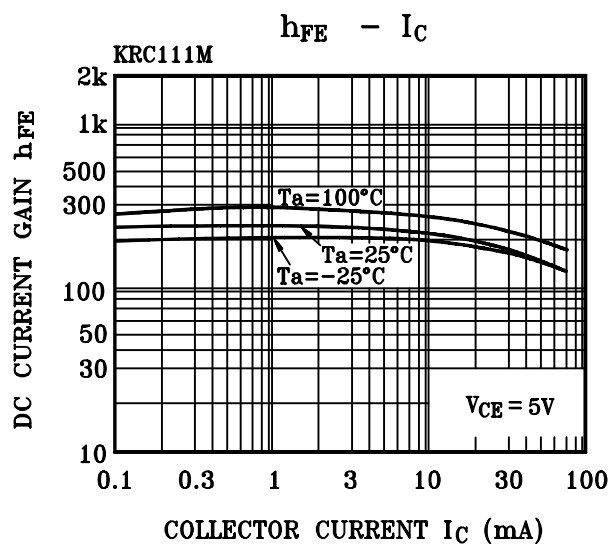
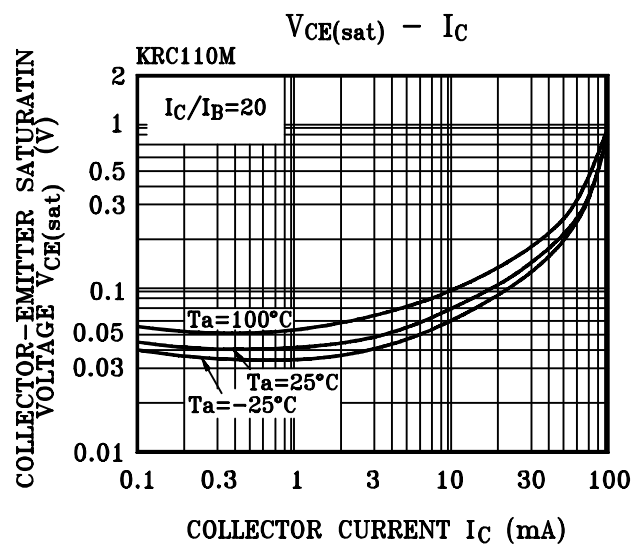
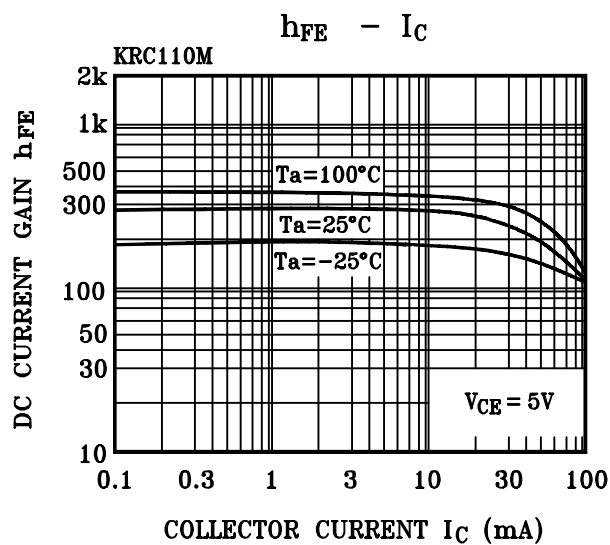
KRC110M~KRC114M

ELECTRICAL CHARACTERISTICS(Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=50V, I_E=0$	–	–	100	nA
Emitter Cut-off Current		I_{EBO}	$V_{EB}=5V, I_C=0$	–	–	100	nA
DC Current Gain		h_{FE}	$V_{CE}=5V, I_C=1mA$	120	–	–	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=10mA, I_B=0.5mA$	–	0.1	0.3	V
Transition Frequency		f_T *	$V_{CE}=10V, I_C=5mA$	–	250	–	MHz
Input Resistor		KRC110M		–	4.7	–	kΩ
		KRC111M		–	10	–	
		KRC112M		–	100	–	
		KRC113M		–	22	–	
		KRC114M		–	47	–	
Switching Time	Rise Time	KRC110M	$V_O=5V$ $V_{IN}=5V$ $R_L=1kΩ$	–	0.025	–	μS
		KRC111M		–	0.03	–	
		KRC112M		–	0.3	–	
		KRC113M		–	0.06	–	
		KRC114M		–	0.11	–	
	Storage Time	KRC110M		–	3.0	–	
		KRC111M		–	2.0	–	
		KRC112M		–	6.0	–	
		KRC113M		–	4.0	–	
		KRC114M		–	5.0	–	
	Fall Time	KRC110M		–	0.2	–	
		KRC111M		–	0.12	–	
		KRC112M		–	2.0	–	
		KRC113M		–	0.9	–	
		KRC114M		–	1.4	–	

Note : *Characteristic of Trnsistor Only

KRC110M~KRC114M



KRC110M~KRC114M

